

IN THE CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A silicon focus ring comprising silicon single crystal used as a focus ring in a plasma apparatus, wherein, in order to increase produce an intrinsic heavy metal gettering effect of the focus ring, a concentration of interstitial oxygen contained in the silicon focus ring is not less than  $5 \times 10^{17}$  atoms/cm<sup>3</sup> and not more than  $1.5 \times 10^{18}$  atoms/cm<sup>3</sup>, and a nitrogen concentration in the silicon focus ring is not less than  $5 \times 10^{13}$  number/cm<sup>3</sup> and not more than  $5 \times 10^{15}$  number/cm<sup>3</sup>, the intrinsic gettering effect exceeding a corresponding effect for silicon not doped with interstitial oxygen and nitrogen.

3. (Original) The silicon focus ring according to claim 1, wherein the surface of the silicon focus ring is subjected to etching treatment.

5. (Currently Amended) A producing method for a silicon focus ring of a single crystal silicon used for a plasma apparatus, wherein, in order to increase produce an intrinsic heavy-metal gettering effect of the focus ring, a concentration of interstitial oxygen contained in the silicon focus ring is not less than  $5 \times 10^{17}$  atoms/cm<sup>3</sup> and not more than  $1.5 \times 10^{18}$  atoms/cm<sup>3</sup>, the single crystal silicon is grown by a Czochralski method with doping nitrogen, a nitrogen concentration in the silicon focus ring is not less than  $5 \times 10^{13}$  number/cm<sup>3</sup> and not more than  $5 \times 10^{15}$  number/cm<sup>3</sup>, the single crystal silicon is processed in a circle, and a silicon ring is produced, the intrinsic gettering effect exceeding a corresponding effect for silicon not doped with interstitial oxygen and nitrogen.